

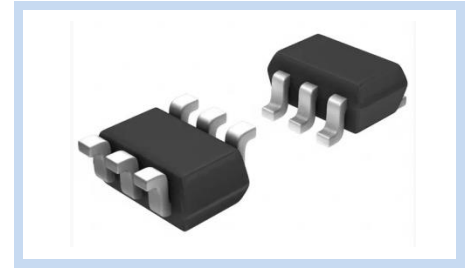
MOSFET SOT-363 Package

MFT-S363

MERITEK

FEATURE

- Operating and Storage Temperature: -50°C ~ +150°C
- Fast Switching Characteristics
- Improved dv/dt Capability



PART NUMBERING SYSTEM

MFT **3** **N** **2A1** **S363S**
 (1) (2) (3) (4) (5)

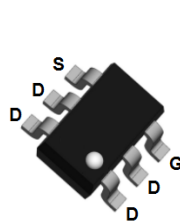


No	Item	Code	Part Description	Series Reference
(1)	Meritek Series	MFT	Meritek MOSFET Series	Surface Mount Type
(2)	Voltage Rating	3	3: 30V	Drain-Source Voltage, 10:100V
(3)	FET Type	N	N: Single N Channel	Dual N-Channel, Dual P-Channel, Dual N+P-Channel MOSFET
(4)	Current Rating	2A1	2A1: 2.1A	Continuous Drain Current, T _C =25°C
(5)	Internal Code	S363S	Internal Control Reference	Package or Project Reference

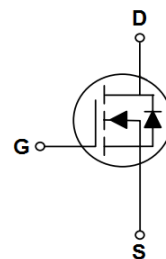
SURFACE MOUNT MOSFET PACKAGE REFERENCE TABLE

Series	FET Type	Channel/ Feature	Continuous Drain Current (I _D) @ 25°C	R _{DS(ON)} Max. @ 4.5 V _{GS}	Power Dissipation (P _D) @25°C	Drain to Source Voltage (V _{DS})
MFT(N)-S363	N	Single	2.1A	66mΩ	0.278W	30V
MFT(2N)-S363E	N+N	Dual/ESD	0.8A	300mΩ	0.275W	20V
MFT(2P)-S363E	P+P	Dual/ESD	0.54	600mΩ	0.278	-20V
MFT(NP)-S363E	N+P	Dual/ESD	0.4 ~ 0.8A	300 ~ 600mΩ	0.275W	-20V, 20V

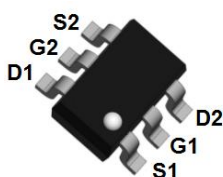
PIN CONFIGURATION



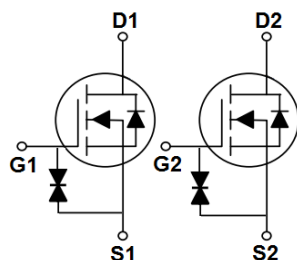
SOT-363



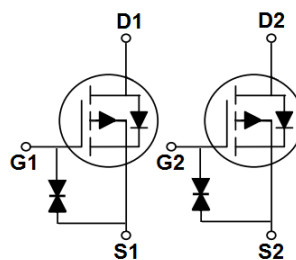
Single N Type



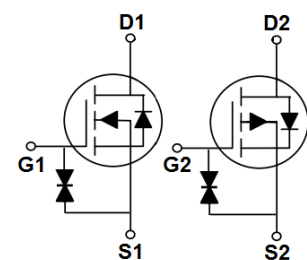
SOT-323



Dual N Type ESD



Dual P Type ESD



Dual N+P Type ESD

MOSFET SOT-363 Package

MFT-S363

MERITEK

ELECTRICAL CHARACTERISTICS

MFT(N)-S363 Series – Single N Channel Type

Part Number	V _{DS} (V)	I _D (A)		V _{GS} (V)	R _{DS(ON)} (mΩ) max. at V _{GS}		Q _g (nC)		CISS (pF)	P _D (W) @25°C	T _S , T _J (°C)
		25°C	100°C		10V	4.5V	10V	4.5V			
MFT3N2A1S363S	30	2.1	-	±20	33/40	51/66	3.1	-	245	0.278	-50 ~ +150

MFT(2N)-S363E Series – Dual N Channel ESD Type

Part Number	V _{DS} (V)	I _D (A)		V _{GS} (V)	R _{DS(ON)} (mΩ) max. at V _{GS}		Q _g (nC)		CISS (pF)	P _D (W) @25°C	T _S , T _J (°C)
		25°C	100°C		10V	4.5V	10V	4.5V			
MFT22NA8S363ES	20	0.8	0.51	±8	-	200/300	-	1	38.2	0.275	-55 ~ +150

MFT(2P)-S363E Series – Dual P Channel ESD Type

Part Number	V _{DS} (V)	I _D (A)		V _{GS} (V)	R _{DS(ON)} (mΩ) max. at V _{GS}		Q _g (nC)		CISS (pF)	P _D (W) @25°C	T _S , T _J (°C)
		25°C	100°C		10V	4.5V	10V	4.5V			
MFT22PA54S363ES	-20	0.54	-	±8	-	440/600	-	1	40	0.278	-55 ~ +150

MFT(NP)-S363E Series – Dual N+P Channel ESD Type

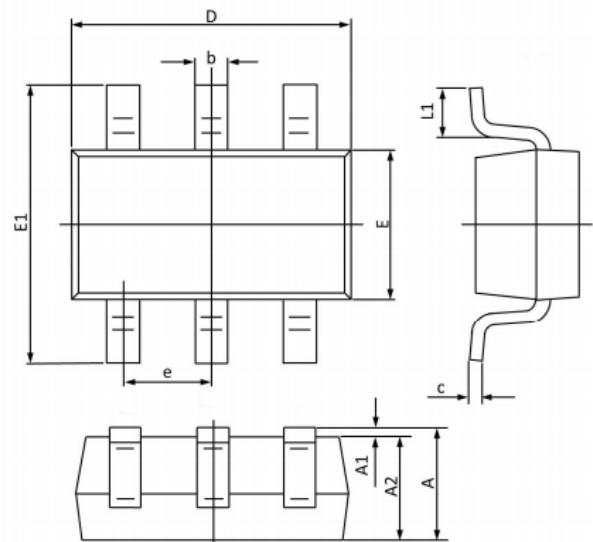
Part Number	V _{DS} (V)	I _D (A)		V _{GS} (V)	R _{DS(ON)} (mΩ) max. at V _{GS}		Q _g (nC)		CISS (pF)	P _D (W) @25°C	T _S , T _J (°C)
		25°C	100°C		10V	4.5V	10V	4.5V			
MFT2NPA8S363ES	20	0.8	0.51	±8	-	200/300	-	1	38.2	0.275	-55 ~ +150
	-20	0.4	0.25	±8	-	440/600	-	1	40	0.275	-55 ~ +150

Note:

1. TA=25°C unless otherwise specified. 2. PD is Power Dissipation Derate above 25°C.

DIMENSIONS

Item	Min. (mm)	Max. (mm)
A	0.800	1.100
A1	0.000	0.100
A2	0.800	1.000
b	0.100	0.330
c	0.100	0.250
D	1.800	2.200
E	1.150	1.350
E1	1.800	2.400
e	0.65 BSC	
L1	0.100	0.350



*Specifications subject to change without notice.